

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. Unknown 9/256643
	INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	
	Applicant: Leonard Forbes et al.	Filing Date: Herewith
		Group: Unknown 2822

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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>mt</i>	5,886,368	03/23/1999	Forbes, L., et al.	257	77	07/29/97
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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes   No
<i>mt</i>	08-255878-TR	10/01/1996	Japan	H01L	27/10	X

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Sheet 1 of 1

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. 09/256,643
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: February 23, 1999	Group: 2822

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<i>M</i>	4,849,797	07/18/1989	Ukai, Y., et al.	357	237	01/20/88

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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes   No

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(Including Author, Title, Date, Pertinent Pages, Etc.)

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Examiner	<i>Michael Trind</i>	Date Considered	<i>8/20/00</i>
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Sheet 1 of 1

Form 1449\*

Atty. Docket No.: 303.324US2

Serial No. 09/256,643

INFORMATION DISCLOSURE STATEMENT  
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Applicant: Leonard Forbes et al.

Filing Date: February 23, 1999

Group: 2822

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MT	5,049,950	09/17/1991	Fujii, Y., et al.	357	2	08/09/90

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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes   No
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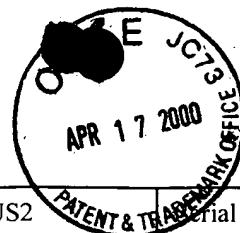
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Sheet 1 of 1

Form 1449*	Atty. Docket No.: 303.324US2	
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(Use several sheets if necessary)		Filing Date: February 23, 1999
		Group: 2822

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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes   No
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OTHER DOCUMENTS

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